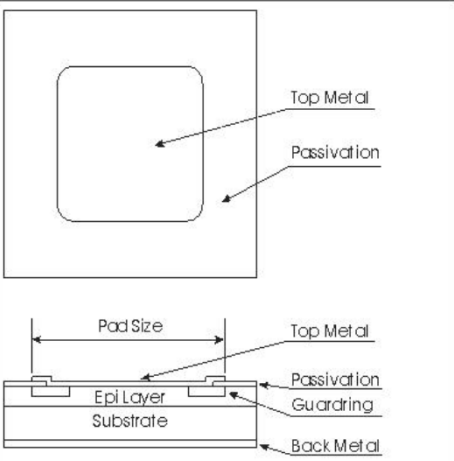


# TRENCH SCHOTTKY DIODE SPECIFICATION

PART NO.	Document ID	DATE	REV.
Y65L05G045	CS-1Y06515	2016/10/20	B

Item	Characteristics	
	Chip Size	1642 x 1642 um
Pad Size	1545 x 1545 um	60.8 x 60.8 mil
Chip Thickness	266.7~292.1 um	10.5~11.5 mil
Scribe Line Width	30 um	1.18 mil
Wafer Size	150 um	6 inch
Passivation	SiO <sub>2</sub>	
Top Metallization	Ag	
Back Metallization	Ag	



## Maximum Ratings (T<sub>A</sub> = 25°C unless otherwise specified).

Item	Symbol	Max. Rating	Unit
Working Peak Reverse Voltage	V <sub>RWM</sub>	45	V
Forward Rectified Current	I <sub>o</sub>	5	A
Forward Surge Current (Note1, 2)	I <sub>FSM</sub>	100	A
Operating Junction Temperature	T <sub>J</sub>	-50~+125	°C
Storage Temperature	T <sub>STG</sub>	-50~+150	°C

## Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise specified).

Item	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Breakdown Voltage	V <sub>B</sub>	46			V	I <sub>R</sub> = 0.5 mA
Reverse Current	I <sub>R</sub>			160	uA	V <sub>R</sub> = 45 V
Forward Voltage Drop (Note1)	V <sub>F</sub>			420	mV	I <sub>F</sub> = 5 A

Note1: Chip packaged in TO-277B (T<sub>a</sub>=25°C). For packaging details please contact us.

Note2: I<sub>FSM</sub> testing condition - 8.3ms single half sine-wave superimposed on rate load (JEDEC method)